L Number	Hits	Search Text	DB	Time stamp
76	10	bozler.in. and remov$3 near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:46
77	6	(GaN or gallium adj nitride) same lateral near5 overgrow$5 and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:48
78	9	(GaN or gallium adj nitride) same overgrow$5 and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:49
79	1	(GaN or gallium adj nitride) same Elo and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:49
80	85	(GaN or gallium adj nitride) same lateral and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:50
81	4438	lateral near4 (grow$4 or over$1grow$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:52
82	436	lateral near4 (grow$4 or over$1grow$4) same (Gan or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:52
83	18	lateral near4 (grow$4 or over$1grow$4) same (Gan or gallium adj nitride) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:00
84	680	(gan or gallium adj nitride) near10 (single near2 crystal$) near5 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:04
85	47	(gan or gallium adj nitride) near10 (single near2 crystal$) near5 (film or layer) same mask$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:09
86	0	later$4 near3 overgrow$4 same "iii-v" and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:09
87	317	later$4 near3 overgrow$4 and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:10
88	120	later$4 near3 overgrow$4 same crystal$ and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:10
89	67	later$4 near3 overgrow$4 same crystal$ near4 single and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:11

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90	10	(later$4 near3 overgrow$4 same crystal$ near4 single and @py<2000) and "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:14
91	227	"iii-v" near10 (gan or gallium adj nitride) near10 (gaas or gallium adj arsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:14
92	22	"iii-v" near10 (gan or gallium adj nitride) near10 (gaas or gallium adj arsenide) and @py<1995	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:14
121	13	useful near10 (Gan or gallium adj nitride) and @py<1995	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:13
122	644	(gan or gallium adj nitride) near10 (single near2 crystal$ or epitax$) near10 sapphire near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:52
123	36	((gan or gallium adj nitride) near10 (single near2 crystal$ or epitax$) near10 sapphire near5 substrate) and @py<1995	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:15
124	142	(gan or gallium adj nitride) near10 (single near2 crystal$ or epitax$) near10 (Gaas or gallium adj arsenide) near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:53
125	7	(gan or gallium adj nitride) near10 (single near2 crystal$ or epitax$) near10 (Gaas or gallium adj arsenide) near5 substrate and @py<1995	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:55
–	156	(remov$4 near5 substrate near10 ((gaas or gallium near3 arsenide) or (sapphire or "al.sub.2o.sub.3")) same (gallium adj nitride or gan)) not ((((gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate same (gallium adj nitride or gan)) and 117$.ccls.) ((((gaas or gallium near3 arsenide) near15 (sapphire or "al.sub.2o.sub.3") near5 substrate) same (gallium adj nitride or gan)) and 117$.ccls.) (sacrific$4 near5 substrate near10 (gaas or gallium near3 arsenide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 15:06
–	2	5334277.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 15:14
–	4	3634149.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 15:14
–	140	117/915.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/27 14:56

—	16	117/915.ccls. and (gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/27 14:57
—	1755	substrate near5 remov$5 and (gan or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/27 14:58
—	1175	substrate near5 remov$5 and (gan or gallium adj nitride) near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/27 14:58
—	608	substrate near5 remov$5 and (gan or gallium adj nitride) near10 (epitax$5 or single near3 crystal$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/27 14:59
—	188	substrate near5 remov$5 same (gan or gallium adj nitride) near10 (epitax$5 or single near3 crystal$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/27 14:59
—	125	substrate near2 remov$5 same (gan or gallium adj nitride) near10 (epitax$5 or single near3 crystal$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/27 15:00
—	6	("4622083" "4727047" "4931132").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/27 15:01